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N-Channel 20 V (D-S) MOSFET

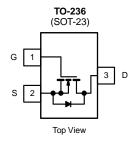
| PRODUCT SUMMARY | | | | | |
|--|--------|--|--|--|--|
| V _{DS} (V) | 20 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$ | 0.024 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 2.5 V$ | 0.033 | | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 1.5 V$ | 0.042 | | | | |
| I _D (A) | 5.2 | | | | |
| Configuration | Single | | | | |

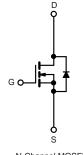
FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^c
- 100 % $R_{\rm q}$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS COMPLIANT HALOGEN FREE





N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \text{ °C}$, unless otherwise noted) | | | | | |
|---|-------------------------|-----------------------------------|---------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V _{DS} | 20 | V | |
| Gate-Source Voltage | | V _{GS} | ± 8 | v | |
| Continuous Drain Current | T _C = 25 °C | I | 5.2 | | |
| | T _C = 125 °C | ID | 3.5 | | |
| Continuous Source Current (Diode Conductio | I _S | 2.5 | А | | |
| Pulsed Drain Current ^a | | I _{DM} | 16 | | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 10 | | |
| Single Pulse Avalanche Energy | L = 0.1 mH | E _{AS} | 5 | mJ | |
| Maximum Power Dissipation ^a | T _C = 25 °C | D | 2 | W | |
| | T _C = 125 °C | P _D | 0.6 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to + 175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------|------------------------|-------------------|-------|------|--|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | | |
| Junction-to-Ambient | PCB Mount ^b | R _{thJA} | 175 | °C/W | | |
| Junction-to-Foot (Drain) | | R _{thJF} | 75 | 0/10 | | |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT | |
|---|--------------------------|--|---|------|-------|-------|------|--|
| Static | • | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 V, I_D = 250 \mu A$ | | 20 | - | - | V | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$ | | - | 1.5 | | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | $V_{DS} = 0 V$, $V_{GS} = \pm 8 V$ | | - | ± 100 | nA | |
| | | $V_{GS} = 0 V$ | V _{DS} = 20 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{GS} = 0 V$ | V _{DS} = 20 V, T _J = 125 °C | - | - | 50 | μA | |
| | | $V_{GS} = 0 V$ | V _{DS} = 20 V, T _J = 175 °C | - | - | 150 | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{GS} = 4.5 V$ | $V_{DS} \ge 5 V$ | 5 | - | - | А | |
| | | $V_{GS} = 4.5 V$ | I _D = 3 A | - | 0.024 | 0.027 | Ω | |
| | | $V_{GS} = 4.5 V$ | I _D = 5 A, T _J = 125 °C | - | - | 0.045 | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 4.5V$ | I _D = 5 A, T _J = 175 °C | - | - | 0.054 | | |
| | | V _{GS} = 2.5 V | I _D = 2 A | - | 0.033 | 0.037 | | |
| | | V _{GS} = 1.5 V | I _D = 1 A | - | 0.042 | 0.047 | | |
| Forward Transconductanceb | 9 _{fs} | V _{DS} = 15 V, I _D = 3 A | | - | 27 | - | S | |
| Dynamic ^b | | | | | • | • | | |
| Input Capacitance | C _{iss} | | | - | 387 | 485 | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ | V _{DS} = 10 V, f = 1 MHz | - | 80 | 100 | | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 37 | 46 | | |
| Total Gate Charge ^c | Qg | | | - | 4.5 | 8.5 | | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 4.5 V | $_{\rm S}$ = 4.5 V V _{DS} = 10 V, I _D = 3 A | | 0.4 | - | nC | |
| Gate-Drain Charge ^c | Q _{gd} | | | | 0.7 | - | | |
| Gate Resistance | R _g | f = 1 MHz | | 6 | 12 | 18 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | - | 7 | 11 | | |
| Rise Time ^c | tr | $\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 10 \; V, \; R_{\text{L}} = 2.5 \; \Omega \\ I_{\text{D}} \cong 4 \; A, \; V_{\text{GEN}} = 4.5 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$ | | - | 8 | 12 | - ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 21 | 32 | | |
| Fall Time ^c | t _f | | | - | 9 | 14 | | |
| Source-Drain Diode Ratings and Char | acteristics ^b | | | | | • | | |
| Pulsed Current ^a | I _{SM} | | | - | | 16 | Α | |
| Forward Voltage | V _{SD} | $I_{\rm F} = 3 \text{ A}, V_{\rm GS} = 0 \text{ V}$ | | - | 0.75 | 1.2 | V | |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

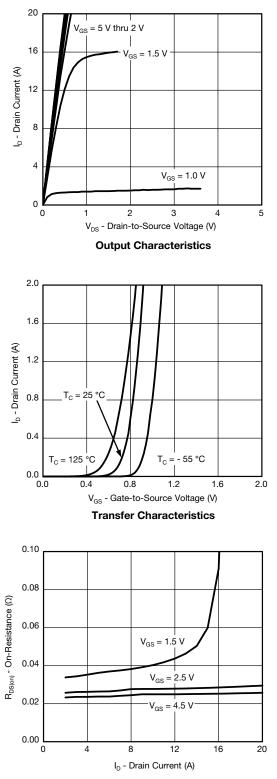
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

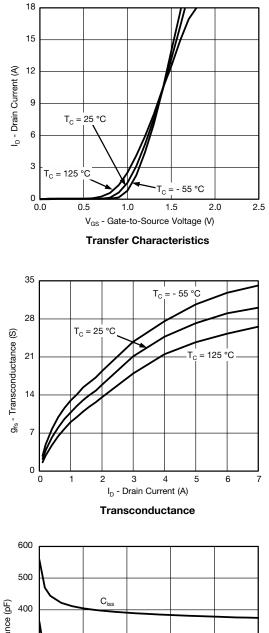
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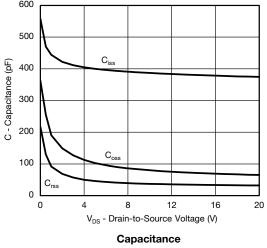
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On-Resistance vs. Drain Current

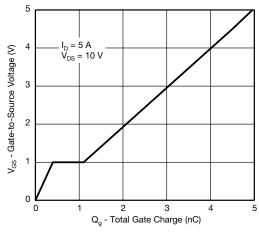




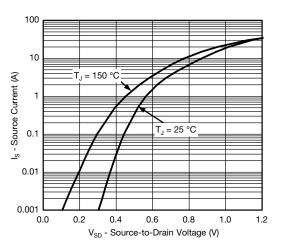
DTS2300S

TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

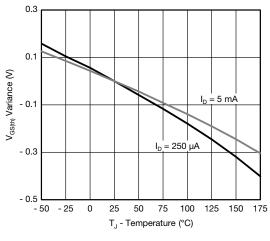
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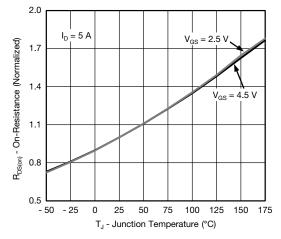
Gate Charge



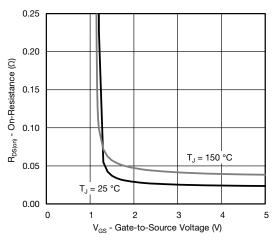
Source Drain Diode Forward Voltage



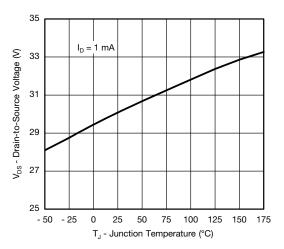
Threshold Voltage



On-Resistance vs. Junction Temperature

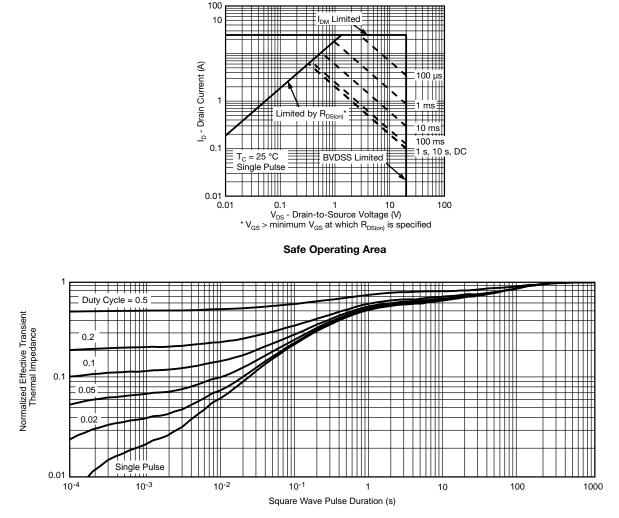


On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

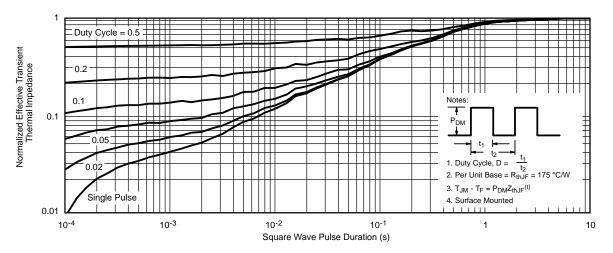
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

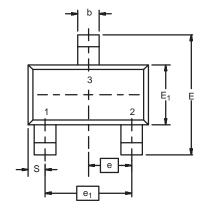
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

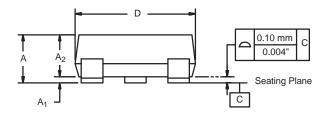
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

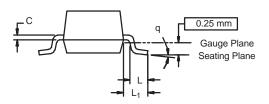
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOT-23 (TO-236): 3-LEAD



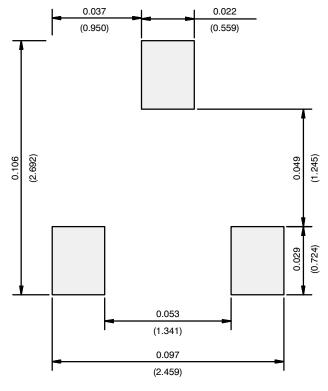




| Dim | MILLIN | IETERS | INCHES | | |
|----------------|----------|--------|------------|-------|--|
| | Min | Мах | Min | Max | |
| Α | 0.89 | 1.12 | 0.035 | 0.044 | |
| A ₁ | 0.01 | 0.10 | 0.0004 | 0.004 | |
| A ₂ | 0.88 | 1.02 | 0.0346 | 0.040 | |
| b | 0.35 | 0.50 | 0.014 | 0.020 | |
| C | 0.085 | 0.18 | 0.003 | 0.007 | |
| D | 2.80 | 3.04 | 0.110 | 0.120 | |
| E | 2.10 | 2.64 | 0.083 | 0.104 | |
| E ₁ | 1.20 | 1.40 | 0.047 | 0.055 | |
| е | 0.95 BSC | | 0.0374 Ref | | |
| e ₁ | 1.90 BSC | | 0.0748 Ref | | |
| L | 0.40 | 0.60 | 0.016 | 0.024 | |
| L ₁ | 0.64 Ref | | 0.025 Ref | | |
| S | 0.50 Ref | | 0.020 Ref | | |
| q | 3° | 8° | 3° | 8° | |
| | 3° | | | | |



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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